

Abstract of the Disclosure:

Sub A1

A vertically structured semiconductor power module is described. A layer thickness of a substrate of the power module between a pn junction and a metallized back is chosen in such a manner that a space charge region produced in the semiconductor module extends as far as the back when a blocking voltage between a source and a drain electrode is applied before a field strength produced by the applied blocking voltage reaches a critical value.

TOP SECRET

REL/tk